Am9114/9124

1024 x 4 Static RAM

DISTINCTIVE CHARACTERISTICS

- Low operating and standby power
- · Access times down to 200 ns
- Am9114 is a direct plug-in replacement for 2114
- Am9124 pin and function compatible with Am9114 and 2114, plus CS power-down feature
- High output drive 4.0-mA sink current @ 0.4 V —Am9124, 3.2-mA sink current @ 0.4 V---Am9114
- TTL-identical input/output levels

GENERAL DESCRIPTION

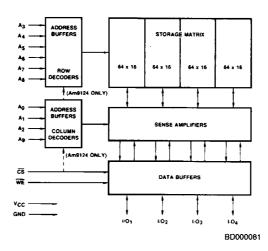
The Am9114 and Am9124 are high-performance, static, N-Channel, read/write, random-access memories organized as 1024 x 4. Operation is from a single 5-V supply, and all input/output levels are identical to standard TTL specifications. Low-power versions of both devices are available with power savings of over 30%. The Am9114 and Am9124 are the same except that the Am9124 offers an automatic CS power-down feature.

The Am9124 remains in a low-power standby mode as long as $\overline{\text{CS}}$ remains HIGH, thus reducing its power requirements.

The Am9124 power decreases from 368 mW to 158 mW in the standby mode, and the Am91L24 from 262 mW to 105 mW. The $\overline{\text{CS}}$ input does not affect the power dissipation of the Am9114.

Data readout is not destructive and the same polarity as data input. \overline{CS} provides for easy selection of an individual package when the outputs are OR-tied. The outputs of 4.0 mA for Am9124 and 3.2 mA for Am9114 provides increased short-circuit current for improved capacitive drive.

BLOCK DIAGRAM

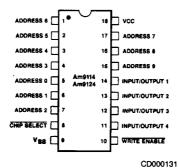


PRODUCT SELECTOR GUIDE

Part Number Speed Indicator Maximum Access Time (ns)			Am9114, Am912	Am9114/91L14	
			В	С	E
			450	300	200
	I _{CC} (mA)	Standard	70	70	70
		Low-Power	50	50	50
0 to +70°C	IPD (mA) (Note 1)	Standard	30	30	_
		Low-Power	20	20	-
	I _{CC} (mA)	Standard	80	80	80
		Low-Power	60	60	60
-55 to +125°C	IPD (mA)	Standard	33	33	-
(Note 1)		Low-Power	22	22	_

Notes: 1. Am9124/91L24 only.

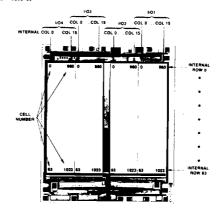
CONNECTION DIAGRAM Top View



Note: Pin 1 is marked for orientation.

BIT MAP

Address Designators					
External	Internal				
A ₀	Ag				
A ₁	A ₈				
A ₂	A ₇				
A ₃	A ₀				
A ₄	A ₁				
A ₅	A ₂				
A ₆	A ₃				
A ₇	A4				
A ₈	A ₅				
Ag	A ₆				

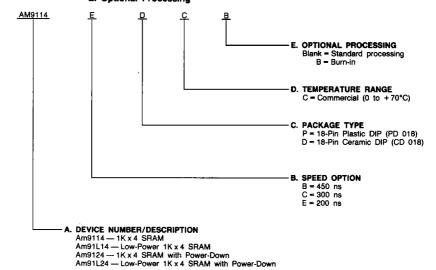


ORDERING INFORMATION (Cont'd.)

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: **A. Device Number**

- B. Speed Option (if applicable)
- C. Package Type
- D. Temperature Range
- E. Optional Processing



Valid Combinations				
AM9114B				
AM91L14B	1			
AM9124B	1			
AM91L24B	1			
AM9114C	PC, PCB,			
AM91L14C	DC, DCB			
AM9124C	1			
AM91L24C	1			
AM9114E	1			
AM91L14E	<u></u> .			

Valid Combinations

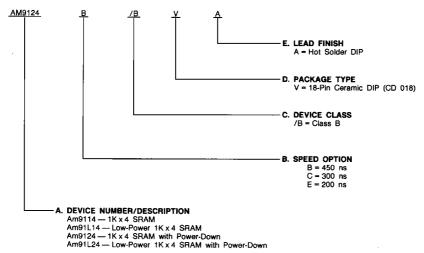
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

ORDERING INFORMATION

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. CPL (Controlled Products List) products are processed in accordance with MIL-STD-883C, but are inherently non-compliant because of package, solderability, or surface treatment exceptions to those specifications. The order number (Valid Combination) for APL products is formed by a combination of: A. Device Number

- B. Speed Option (if applicable)
- C. Device Class
- D. Package Type
- E. Lead Finish



Valid Combinations			
AM9114B			
AM91L14B			
AM9124B			
AM91L24B	/BVA		
AM9114C	7847		
AM91L14C			
AM9124C			
AM91L24C			
AM9114E			
AM91L14E			

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

PIN DESCRIPTION

A₀ - A₉ Address Inputs

The address input lines select the memory location from which to read or write.

CS Chip Select (Input, Active LOW)

The $\overline{\text{CS}}$ line selects the memory device for active operation.

WE Write Enable (Input, Active LOW)

When both CS and WE are LOW, data on the input lines is written to the location presented on the address input lines.

I/O₁-i/O₄ Data in/Out Bus (Bidirectional)

These lines provide the path for data to be written to or read from the selected memory location.

V_{CC} Power Supply

V_{SS} Ground

TABLE 1. SUPPLY CURRENT ADVANTAGE OF Am9124

		Worst Case Current (mA at 0°C)			
Configuration	Part	100%	50%		
	Number	Duty Cycle	Duty Cycle		
2K x 8	9114	280	280		
	91L14	200	200		
20.00	9124	200	160		
	91L24	140	110		
4K x 12	9114	840	840		
	91L14	600	600		
4N X 12	9124	480	420		
	91L24	330	285		
8K x 16	9114	2240	2240		
	91L14	1600	1600		
ON X 10	9124	1120	1040		
	91L24	760	700		

ABSOLUTE MAXIMUM RATINGS (Note 1)

Storage Temperature	65 to +150°C
Ambient Temperature with	
Power Applied	55 to +125°C
Supply Voltage	0.5 V to +7.0 V
Signal Voltages with	
Respect to Ground	0.5 V to +7.0 V
Power Dissipation	1.0 W
DC Output Current	10 mA

The products described by this specification include internal circuitry designed to protect input devices from damaging accumulations of static charge. It is suggested nevertheless, that conventional precautions be observed during storage, handling and use in order to avoid exposure to excessive voltages.

OPERATING RANGES (Note 2)

Commercial (C) Devices	
Temperature	0°C to +70°C
Supply Voltage	
Military (M) Devices*	
Temperature	55°C to +125°C
Supply Voltage	+4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

*Military products 100% tested at $T_c = +25$ °C, +125°C and -55°C

DC CHARACTERISTICS over operating range unless otherwise specified*

Parameter Symbol	Parameter Description		Test Conditions		Min.	Max.	Unit
Юн	Output HIGH Current	V _{CC} = +4.5V	V _{CC} = +4.5V 91(L)14		-1.0	_	
	ootpar man ounem	V _{OH} = 2.4V	91(L)24		-1.4		
			T 70°C	91(L)14	3.2		mA
loL	Output LOW Current	VOL = 0.4V	T _A = 70°C	91(L)24	4.0		
	1	VOL - 0.44		91(L)14	2.4		
			1A - + 125 C	91(L)24	3.2		
V _{IH}	Input HIGH Voltage				2.0	Vcc	
_ V _{IL}	Input LOW Voltage				-0.5	0.8	V
lix	Input Load Current	V _{SS} ≤ V _{IN} ≤ V _{CC}			1	10	
loz	Output Leakage Current	V _{SS} ≤ V _O ≤ V _{CC} ,	TA = 0 to +70°C		-10	10	μΑ
		Output Disabled	Output Disabled T _A = -55 to +125°C		-50	50	
	Output Short Circuit Current		91(L)14C			75	
los		(Note 3)	91(L)24C		1	95	
00			91(L)14M			75	mA
			91(L)24M			115	ĺ
				Standard devices		70	
lcc '	Operating Supply Current	V _{CC} = Max.	T _A = 0°C	L devices	T	50	
	Operating Supply Current	CS ≤ V _{IL}	T _A = -55°C	Standard devices L devices		80 60	
			9124		30	mΑ	
IPD	Automatic CS Power Down Current (9124/L24 only) CS ≥ V _{IH} T _A = 0°C		TA = 0°C	91L24		20	
·FD		-	9124		33	ı	
			T _A = -55°C	91L24		22	
CIN	Input Capacitance	(Nata 2)	f = 1.0 MHz,			7	
C _{I/O}	I/O Capacitance	(Note 7)	T _A = 25°C, All pins at 0 V			7	ρF

Notes: 1. Absolute Maximum Ratings are intended for user guidelines and are not tested.

2. For test and correlation purposes, ambient temperature is defined as the stabilized case temperature.

3. For test purposes, not more than one output at a time should be shorted. Short-circuit test duration should not exceed 30 seconds. Actual testing is performed for only 5 ms.

4. Test conditions assume signal transition times of 10 ns or less, timing reference levels of 1.5 V and output loading of one standard TTL gate

plus 100 pf.

5. The internal write time of the memory is defined by the overlap of CS LOW and WE LOW. Both signals must be LOW to initiate a write and bold timing should be referenced to the rising edge of the signal. either signal can terminate a write by going HIGH. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

6. Chip Select access time (t_{CO}) is longer for the Am9124 than for the Am9114. The specified address access time will be valid only when Chip

Select is low soon enough for t_{CO} to elapse.

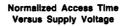
7. These parameters are not 100% tested, but are evaluated at initial characterization and at any time the design is modified where these parameters may be affected.

^{*}See the last page of this spec for Group A Subgroup Testing information.

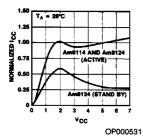
TYPICAL DC and AC CHARACTERISTICS

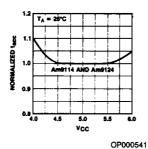
Normalized Supply Current

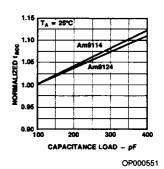
Versus Supply Voltage



Normalized Access Time Versus Output Loading

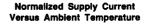


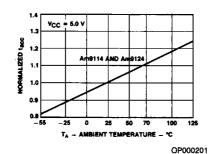




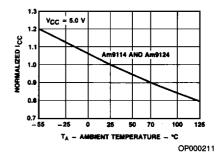
Normalized Access Time

Versus Ambient Temperature







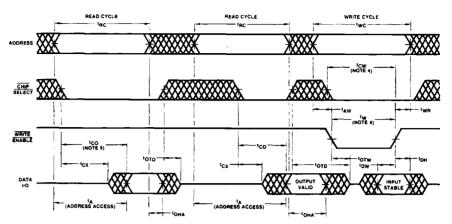


		Parameter Description		B Devices		C Devices		E Devices		
No.	Parameter Symbol			Min.	Max.	Min.	Max.	Min.	Max.	Units
R	ead Cycle									
1	t _{RC}	Address Valid to Address Do Not Care Time (Read Cycle Time)	450		300		200		ns
2	t _A	Address Valid to Data Out Valid Delay (Address Access Time)			450		300		200	ns
3		Chip Select LOW to Data	Am9114		120		100		70	ns
	\$∞	Out Valid (Note 6)	Am9124		420		280		185	ns
4	tcx	Chip Select LOW to Data Out On		10		10		10		ns
5	t OTD	Chip Select HIGH to Data Out Off			100		80		60	ns
6	[‡] OHA	Address Unknown to Data Out Unknown Time		50		50		50		ns
W	rite Cycle									
7	twc	Address Valid to Address Do Not Care Time (Write Cycle Time)		450		300		200		ns
•		Write Enable LOW to Write	Am9114	200		150	_	120		ns
В	tw	Enable HIGH Time (Note 5)	Am9124	250		200		150		ns
9	twn	Write Enable HIGH to Address Do Not Care T	ime	0		0		0		ns
10	torw	Write Enable LOW to Data Out Off Delay			100		80		60	ns
11	tow	Data In Valid to Write Enable HIGH Time		200		150		120		ns
12	t _{DH}	Write Enable HIGH to Data In Do Not Care Ti	me	0		0		0		ns
13	taw	Address Valid to Write Enable LOW Time		0		0		0		ns
14	tPD	Chip Select HIGH to Power LOW Delay (Am91	24 only) (Note 7)		200		150		100	ns
15	tpu	Chip Select LOW to Power HIGH Delay (Am91	24 only) (Note 7)	0		0		0		ns
46		Chip Select LOW to Write	Am9114	200		150		120		90
16	tcw	Enable HIGH Time (Note 5)	Am9124	250		200		150		ns

Notes: See notes following DC Characteristics table

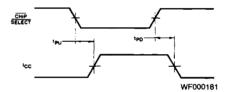
^{*}See the last page of this spec for Group A Subgroup Testing information.

SWITCHING WAVEFORMS



WF000171

Power-Down Waveform (Am9124 Only)



GROUP A SUBGROUP TESTING

DC CHARACTERISTICS

Parameter Symbol	Subgroups
ЮН	1, 2, 3
loL	1, 2, 3
VIH	7, 8
V _{IL}	7, 8
lix	1, 2, 3
loz	1, 2, 3
los	1, 2, 3
lcc	1, 2, 3
I _{PD}	1, 2, 3

SWITCHING CHARACTERISTICS

Parameter Symbol	Subgroups	Parameter Symbol	Subgroups
tac	7, 8, 9, 10, 11	twR	7, 8, 9, 10, 11
tA	7, 8, 9, 10, 11	tотw	7, 8, 9, 10, 11
tco	7, 8, 9, 10, 11	t _{DW}	7, 8, 9, 10, 11
tcx	7, 8, 9, 10, 11	t _{DH}	7, 8, 9, 10, 11
tотр	7, 8, 9, 10, 11	t _{AW}	7, 8, 9, 10, 11
toha	7, 8, 9, 10, 11	t _{PD}	7, 8, 9, 10, 11
twc	7, 8, 9, 10, 11	tpU	7, 8, 9, 10, 11
t _W	7, 8, 9, 10, 11	tcw	7, 8, 9, 10, 11

MILITARY BURN-IN

Military burn-in is in accordance with the current revision of MIL-STD-883, Test Method 1015, Conditions A through E. Test Conditions are selected at AMD's option.